# <u>Silicon Carbide (SiC)</u> <u>MOSFET</u> – 12 mohm, 650 V, M2, TO-247-4L

# NVH4L015N065SC1

#### Features

- Typ.  $R_{DS(on)} = 12 \text{ m}\Omega @ V_{GS} = 18 \text{ V}$ Typ.  $R_{DS(on)} = 15 \text{ m}\Omega @ V_{GS} = 15 \text{ V}$
- Ultra Low Gate Charge ( $Q_{G(tot)} = 283 \text{ nC}$ )
- High Speed Switching with Low Capacitance ( $C_{oss} = 430 \text{ pF}$ )
- 100% Avalanche Tested
- AEC-

#### Table 1. THERMAL CHARACTERISTICS

Parameter	Symbol	Мах	Unit
Junction-to-Case - Steady State (Note 1)	$R_{\theta JC}$	0.3	°C/W
Junction-to-Ambient - Steady State (Note 1)	$R_{\thetaJA}$	40	

## Table 2. ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = $25^{\circ}$ C unless otherwise specified)

Parameter	Symbol Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS						

Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}$		650	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>	$I_D = 20 \text{ mA}$ , referenced to $25^{\circ}C$		-	0.12	-	V/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$\begin{array}{c} V_{GS} = 0 \ V, \\ V_{DS} = 650 \ V \end{array} \qquad \begin{array}{c} T_{J} = 25^{\circ}C \\ T_{J} = 175^{\circ}C \end{array}$		-	-	10	μΑ
				-	-	1	mA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{GS} = +18/-5 \text{ V}, V_{DS} = 0 \text{ V}$		-	-	250	nA

### **ON CHARACTERISTICS** (Note 2)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D = 25 \text{ mA}$	1.8	2.5	4.3	V
Recommended Gate Voltage	V <sub>GOP</sub>		-5	-	+18	V
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	$V_{GS}$ = 15 V, I <sub>D</sub> = 75 A, T <sub>J</sub> = 25°C				

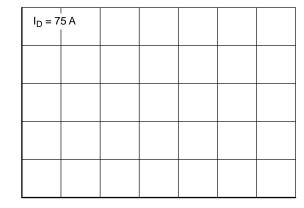
# Table 2. ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = $25^{\circ}$ C unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
SOURCE-DRAIN DIODE CHARACT	ERISTICS					
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = -5/18 \text{ V}, I_{SD} = 75 \text{ A},$	-	28	_	ns
Reverse Recovery Charge	Q <sub>RR</sub>	dl <sub>S</sub> /dt = 1000 A/μs	_	234	-	nC
Reverse Recovery Energy			-	-	-	-

# **TYPICAL CHARACTERISTICS**

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#### TYPICAL CHARACTERISTICS (continued)









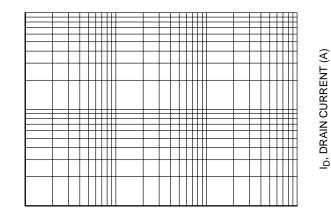
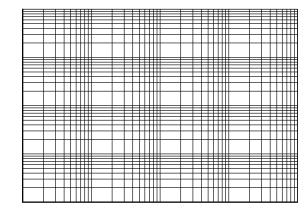




Figure 9. Unclamped Inductive Switching Capability

I<sub>D</sub>, DRAIN CURRENT (A)



V<sub>DS</sub>, DRAIN-TO-SOURCE VOLTAGE (V)

Figure 11. Safe Operating Area

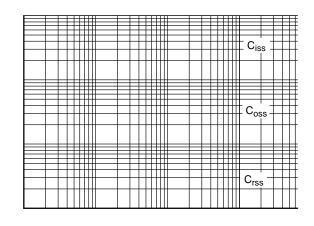
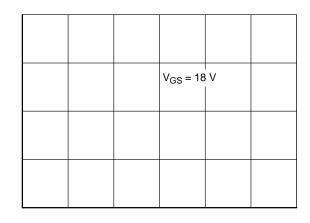


Figure 8. Capacitance vs. Drain-to-Source Voltage



T<sub>C</sub>, CASE TEMPERATURE (°C)

Figure 10. Maximum Continuous Drain Current vs. Case Temperature

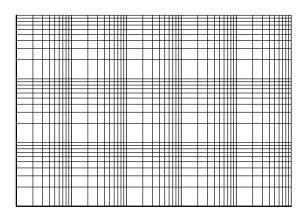
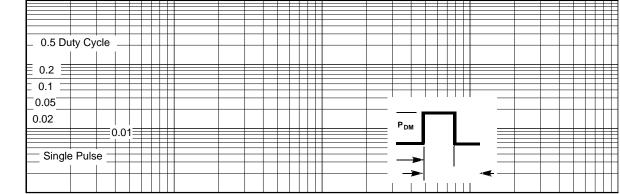


Figure 12. Single Pulse Maximum Power

### TYPICAL CHARACTERISTICS (continued)

 $Z_{\theta,JC}(t).$  EFFECTIVE TRANSIENT THERMAL RESISTANCE (°C/W)



t, RECTANGULAR PULSE DURATION (sec)

Figure 13. Junction-to-Case Thermal Response

			TO-247-4LD CASE 340CJ ISSUE A			DATE 16 SEP 2019
A	E	A	В А2	E1	Øp1 D2	
E/2		Q D	Ø		D1	
b2 b1 (3X)		L	L1 A1			
1 e1 ⊕ 0.254	4 (M) b a (M)	b(4X)	с			

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